(b) a second atmospheric deposition station comprising an atmospheric pressure vapor deposition chamber, wherein the first atmospheric deposition station and the second atmospheric deposition station are coupled together; and

A1 cnt

(c) a substrate handling system adapted to transfer substrates between the first atmospheric deposition station and the second atmospheric deposition station, and

wherein a plasma system is associated with the atmospheric pressure vapor deposition chamber.

A2

5. (Amended) The apparatus of claim 1 wherein the plasma system is a remote plasma system that is adapted to form a plasma upstream of the atmospheric pressure vapor deposition chamber.

A3

9. (Amended) The apparatus of claim 1 wherein the atmospheric pressure vapor deposition chamber is an atmospheric pressure chemical vapor deposition (APCVD) chamber.

A4

11. (Amended) An apparatus for processing semiconductor substrates, the apparatus comprising:

(a) an atmospheric chemical vapor deposition chamber;

(b) a plasma system associated with the atmospheric chemical vapor deposition chamber;

(c) a spin coating chamber coupled to the atmospheric chemical vapor deposition chamber;

(d) a curing station coupled to the atmospheric chemical vapor deposition chamber; and

(e) a substrate handling system adapted to transfer substrates between the atmospheric chemical vapor deposition chamber, the spin coating chamber, and the curing station.